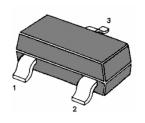


NPN General Purpose Amplifier

For low noise, high gain, general purpose amplifier applications at collector currents from 1µA to 50mA.



1: Base 2: Emitter 3: Collector

Marking: 1RM

SOT-23 Plastic Package

Absolute Maximum Ratings (Ta = 25 ℃)

| | Symbol | Value | Unit |
|--|-----------------------------------|-------------|-------------|
| Collector Emitter Voltage | V _{CEO} | 25 | ٧ |
| Collector Base Voltage | V _{CBO} | 30 | V |
| Emitter Base Voltage | V _{EBO} | 4.5 | ٧ |
| Collector Current - Continuous | Ic | 100 | mA |
| Total Device Dissipation Derate above 25°C | P _{tot} | 200 2.8 | mW mW/°C |
| Thermal Resistance, Junction to Ambient | $R_{\scriptscriptstyle{	hetaJA}}$ | 357 | °C/W |
| Operating and Storage Junction Temperature Range | T _J ,T _S | -55 to +150 | °C |





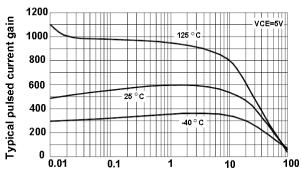
Characteristics at Tamb=25 oC

| | Symbol | Min. | Max. | Unit |
|--|----------------------|------|------|------|
| DC Current Gain | | | | |
| at V _{CE} =5V, I _C =100µA | h _{FE} | 400 | 1200 | - |
| at V _{CE} =5V, I _C =1 mA | h _{FE} | 450 | - | - |
| at V _{CE} =5V, I _C =10mA | h _{FE} | 400 | - | - |
| Small Signal Current Gain | | | | |
| at V _{CE} =5V, I _C =1 mA, f=1KHz | h _{fe} | 450 | 1800 | - |
| Collector Base Breakdown Voltage | | , | | |
| at I _C =100μA | V _{(BR)CBO} | 30 | - | V |
| Collector Emitter Breakdown Voltage | | | | |
| at I _C =1mA | V _{(BR)CEO} | 25 | - | V |
| Collector Emitter Saturation Voltage | | | | |
| at I _C =10mA, I _B =1mA | V _{CEsat} | - | 0.5 | V |
| Base Emitter On Voltage | | | | |
| at I _C =10mA, V _{CE} =5V | V _{B Eon} | - | 0.8 | V |
| Collector Cutoff Current | | | | |
| at V _{CB} =15∨ | Ісво | - | 50 | nΑ |
| Emitter Cutoff Current | | | | |
| at V _{EB} =3∨ | l⊞o | - | 50 | nΑ |
| at V _{EB} =4.5∨ | l⊞o | - | 100 | nΑ |
| Gain Bandwidth Product | | | | |
| at V _{CE} =5V, I _C =500µA, f=20MHz | f _T | 50 | - | MHz |
| Collector Base Capacitance | | | | |
| at V _{CB} =5∨, f = 100KHz | Ссь | - | 4 | pF |
| Emitter Base Capacitance | | | | |
| at V _{BE} =0.5V, f = 100 KHz | Ceb | - | 10 | pF |
| Noise Figure | | | | |
| at V_{CE} =5 V , I_C =100 μ A, R_S =10 $K\Omega$, f = 10 Hz to 15.7 KHz | NF | - | 2 | dB |

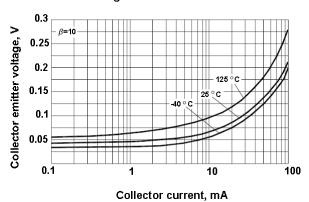




Typical pulsed current gain vs. collector current



Collector emitter saturation voltage vs.collector current



Collector current, mA

Base emitter saturation

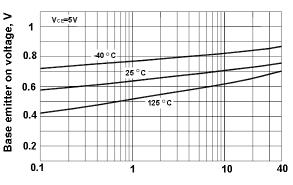
voltage vs.collector current

Base emitter voltage, V -40 ° C 8.0 25 ° C 0.6 0.4 0.2

Collector current, mA

10

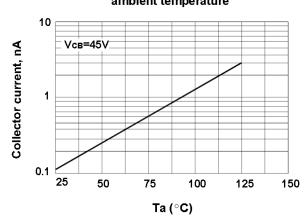
Base emitter on voltage vs.collector current



Collector current, mA

Collector cutoff current vs. ambient temperature

100



SHIKE MAKE CONSCIOUS PRODUCT

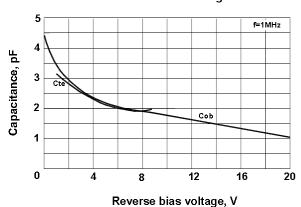
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Conscious Products Begin With Conscious People

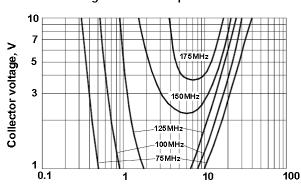




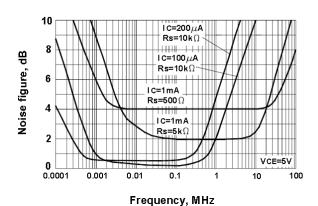
Input and output capacitance vs. reverse bias voltage



Contours of constant gain bandwidth product

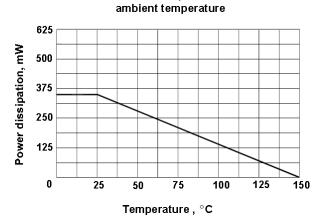


Noise figure vs. frequency

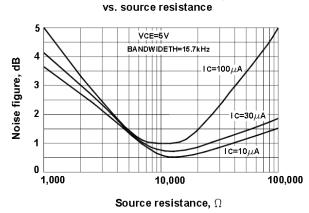


Power dissipation vs.

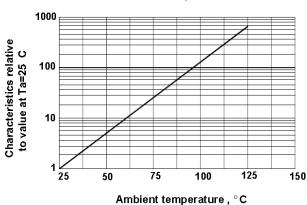
Collector current, mA



Wideband noise frequency



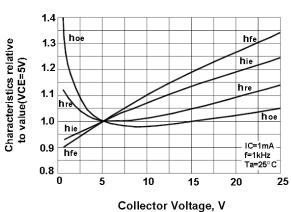
Normalized collector cutoff current vs. ambient temperature



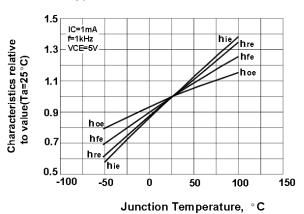




Typical common emitter characteristics



Typical common emitter characteristics



Typical common emitter characteristics

